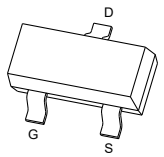
GPTD7N20N

200V N-Channel MOSFET

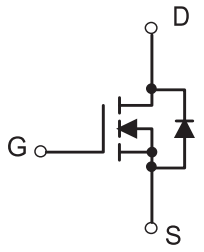
Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
200V	1.3Ω@10V	0.6A

SOT-23



Schematic diagram



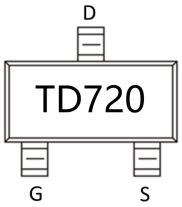
Feature

- Split Gate Trench Technology
- Low $R_{DS(ON)}$
- Low Gate Charge

Application

- Power Switching Application

MARKING:



ABSOLUTE MAXIMUM RATINGS (T_A = 25℃ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	200	V
Gate - Source Voltage		V_{GS}	±20	V
Continuous Drain Current[1,5]	T_A = 25℃	I_D	0.6	A
Pulsed Drain Current[2]		I_{DM}	4.8	A
Power Dissipation[4,5]	T_A = 25℃	P_D	2	W
Thermal Resistance from Junction to Ambient[6]		$R_{\theta JA}$	62.5	℃/W
Junction Temperature		T_J	150	℃
Storage Temperature		T_{STG}	-55~ +150	℃

MOSFET ELECTRICAL CHARACTERISTICS (T_A = 25℃ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V , I_D = 250μA	200			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 200V, V_{GS} = 0V			1	μA
Gate - Body Leakage Current	I_{GSS}	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics[3]						
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250μA	2.0	3.2	4.0	V
Drain-source On-resistance	$R_{DS(on)}$	V_{GS} = 10V, I_D =1A		1.3	1.5	Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	V_{DS} = 100V, V_{GS} = 0V, f =1MHz		120		pF
Output Capacitance	C_{oss}			10		
Reverse Transfer Capacitance	C_{rss}			4		
Gate Resistance	R_g	V_{DS} = 0V, V_{GS} = 0V		1.6		Ω
Switching Characteristics						
Total Gate Charge	Q_g	V_{DS} = 100V, V_{GS} = 10V, I_D = 1.2A		4.7		nC
Gate-source Charge	Q_{gs}			0.7		
Gate-drain Charge	Q_{gd}			2.6		
Turn-on Delay Time	$t_{d(on)}$	V_{DD} =100V, V_{GS} = 10V, I_D = 0.36A, R_G =53Ω		7		ns
Turn-on Rise Time	t_r			8		
Turn-off Delay Time	$t_{d(off)}$			9		
Turn-off Fall Time	t_f			20		
Source - Drain Diode Characteristics						
Diode Forward Voltage[3]	V_{SD}	V_{GS} = 0V, I_S = 1A			1.2	V

Notes :

1.The maximum current rating is limited by package.And device mounted on a large heatsink

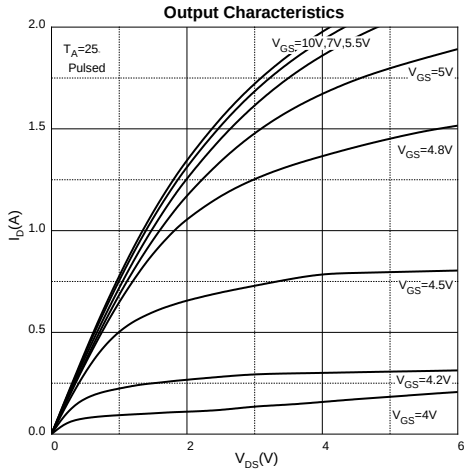
2.Pulse Test : Pulse Width ≤ 10μs, duty cycle ≤ 1%.

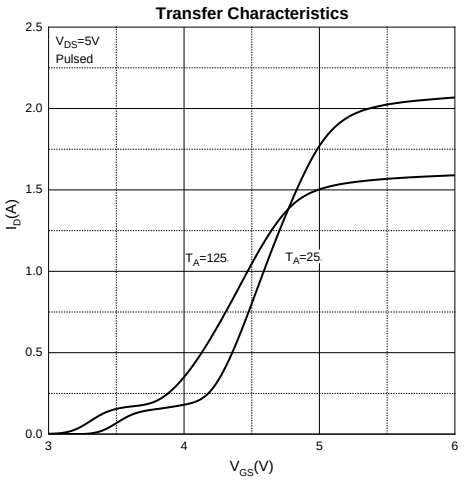
4.Pulse Test : Pulse Width ≤ 300μs, duty cycle ≤ 2%.

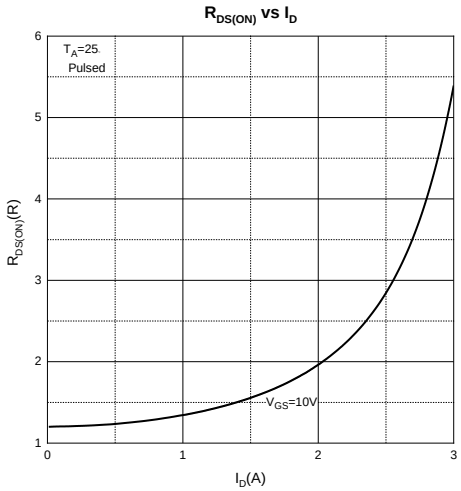
5.The power dissipation P_D is limited by $T_{J(MAX)}$ = 150°C.And device mounted on a large heatsink

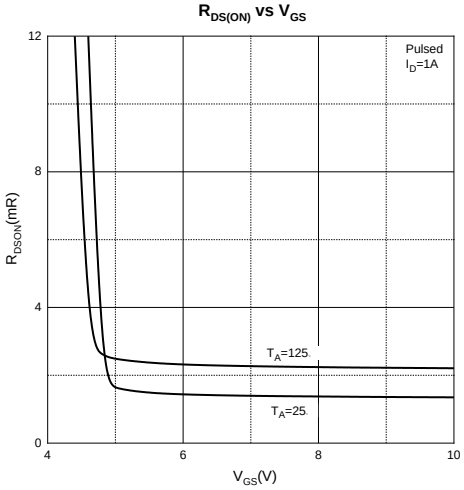
6.Device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C.

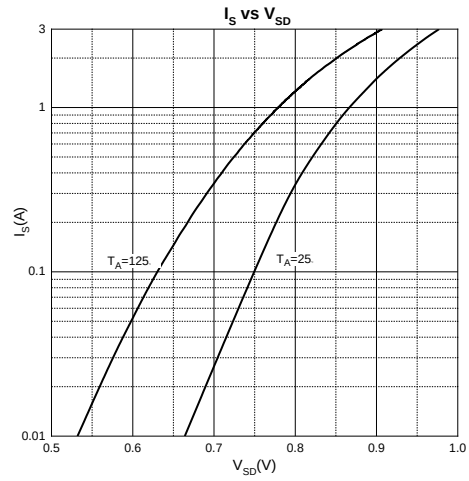
Typical Characteristics

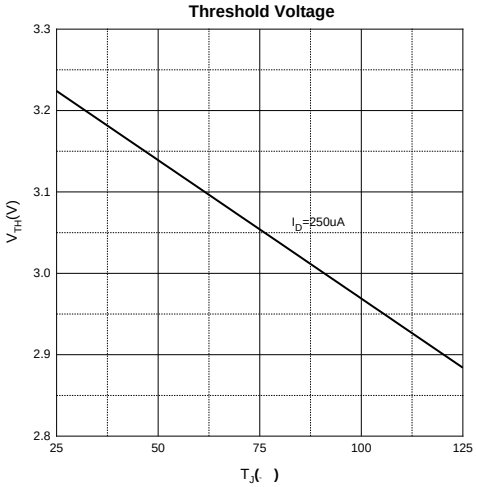




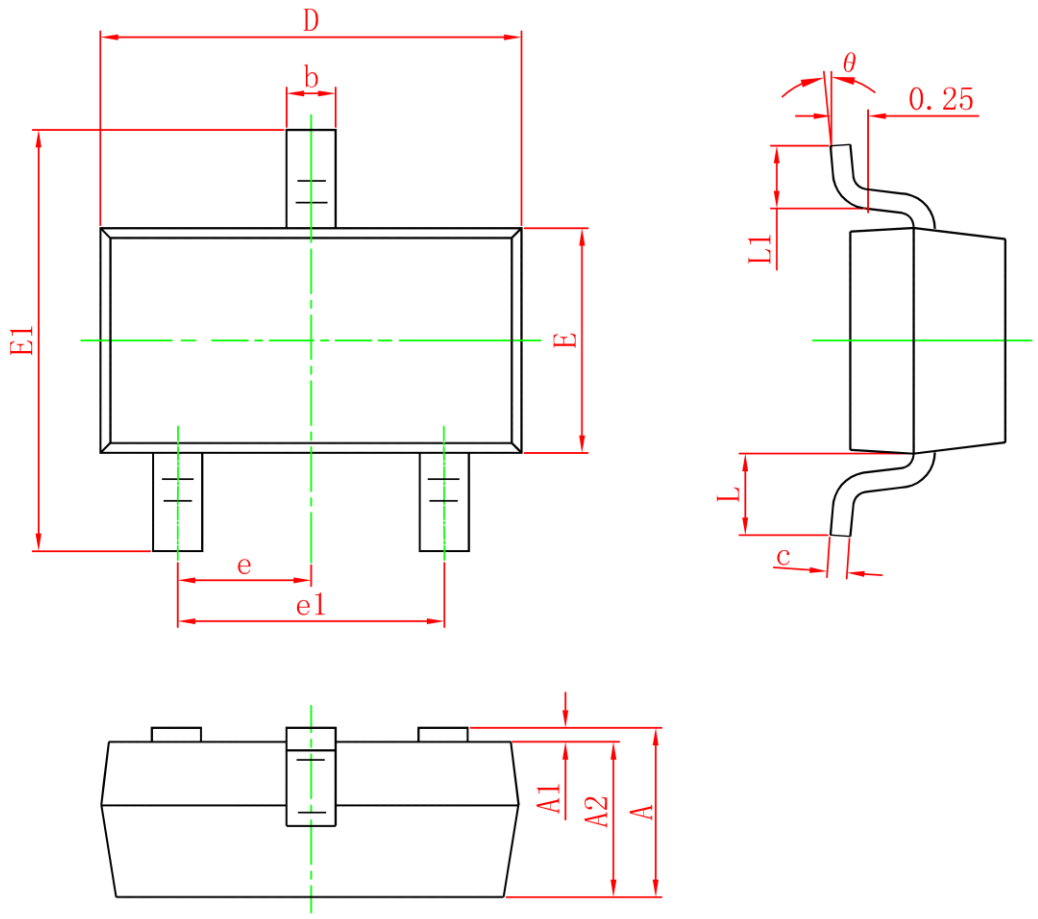








SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0	0.100	0	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.150	1.500	0.045	0.059
E1	2.250	2.650	0.089	0.104
e	0.950TYP		0.037TYP	
e1	1.800	2.000	0.071	0.079
L	0.550REF		0.022REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°